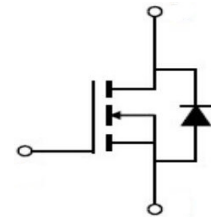
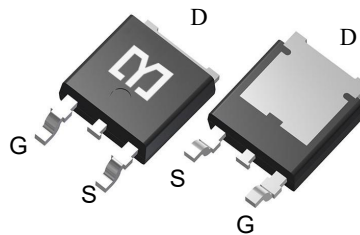


## General Description

MY60N10D series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.



## Features

$V_{DSS}$	100	V
$I_D$	60	A
$R_{DS(ON)}(at V_{GS}=10V)$	<16	m $\Omega$
$R_{DS(ON)}(at V_{GS}=4.5V)$	<27	m $\Omega$

## Application

- Battery protection
- Load switch
- Uninterruptible power supply

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY60N10D	TO-252-2L	0161N	2500

## Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	100	V
Gate source voltage	$V_{GS}$	±20	V
Continuous drain current <sup>1)</sup> , T <sub>c</sub> =25 °C	$I_D$	60	A
Pulsed drain current <sup>2)</sup> , T <sub>c</sub> =25 °C	$I_D$ , pulse	120	A
Power dissipation <sup>3)</sup> , T <sub>c</sub> =25 °C	$P_D$	72	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	270	mJ
Operation and storage temperature	T <sub>stg</sub> , T <sub>j</sub>	-55 to 150	°C

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R $\theta$ JC	2.5	°C/W
Thermal resistance, junction-ambient <sup>4)</sup>	R $\theta$ JA	100	°C/W

**Electrical Characteristics at T<sub>J</sub>=25 °C unless otherwise specified**

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 $\mu$ A	100			V
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 $\mu$ A	1.0		2.5	V
Drain-source on-state resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10 V, I <sub>D</sub> =50 A		13	18	m $\Omega$
Drain-source on-state resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5 V, I <sub>D</sub> =30 A		16	25	m $\Omega$
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =20 V			100 -100	nA
Drain-source leakage current	I <sub>DSS</sub>	V <sub>DS</sub> =100 V, V <sub>GS</sub> =0 V			1	$\mu$ A
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0 V, V <sub>DS</sub> =50 V, f=1 MHz		1300		pF
Output capacitance	C <sub>oss</sub>			194.6		pF
Reverse transfer capacitance	C <sub>rss</sub>			4.1		pF
Turn-on delay time	t <sub>d(on)</sub>		V <sub>GS</sub> =10 V, V <sub>DS</sub> =50 V, R <sub>G</sub> =2.2 $\Omega$ , I <sub>D</sub> =10 A		17.8	
Rise time	t <sub>r</sub>			3.9		ns
Turn-off delay time	t <sub>d(off)</sub>			33.5		ns
Fall time	t <sub>f</sub>			3.2		ns
Total gate charge	Q <sub>g</sub>	I <sub>D</sub> =8 A, V <sub>DS</sub> =50 V, V <sub>GS</sub> =10 V			19.8	
Gate-source charge	Q <sub>gs</sub>			2.4		nC
Gate-drain charge	Q <sub>gd</sub>			5.3		nC
Gate plateau voltage	V <sub>plateau</sub>			3.2		V
Diode forward current	I <sub>S</sub>		V <sub>GS</sub> <V <sub>th</sub>			40
Pulsed source current	I <sub>SP</sub>				120	A
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =8 A, V <sub>GS</sub> =0 V			1.3	V
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> =8 A, di/dt=100 A/ $\mu$ s		50.2		ns
Reverse recovery charge	Q <sub>rr</sub>				95.1	nC
Peak reverse recovery current	I <sub>rrm</sub>				2.5	A

**Note**

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of R $\theta$ JA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25 °C.
- 5) V<sub>DD</sub>=50 V, R<sub>G</sub>=25  $\Omega$ , L=0.3 mH, starting T<sub>J</sub>=25 °C.

**Typical Characteristics**

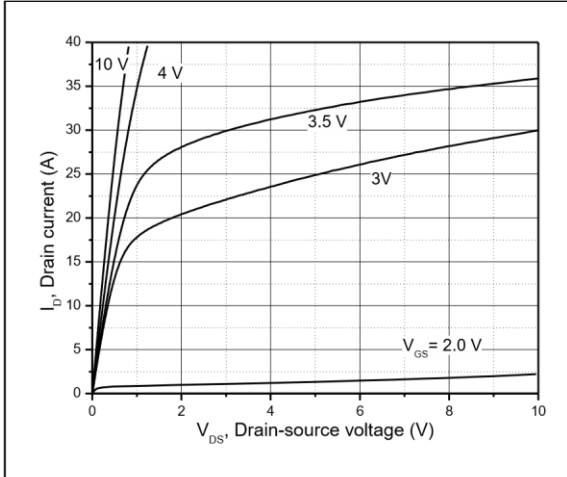


Figure 1, Typ. output characteristics

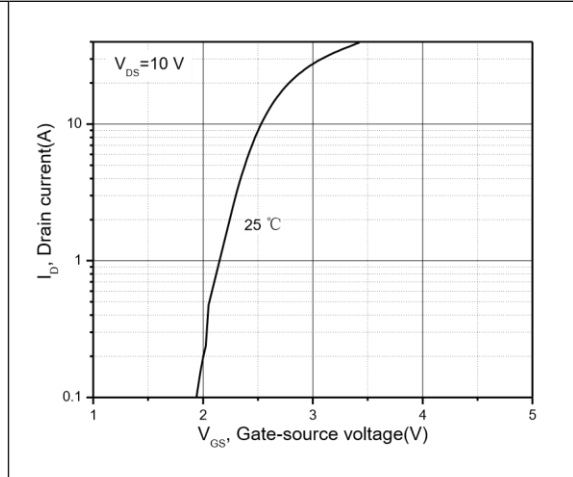


Figure 2, Typ. transfer characteristics

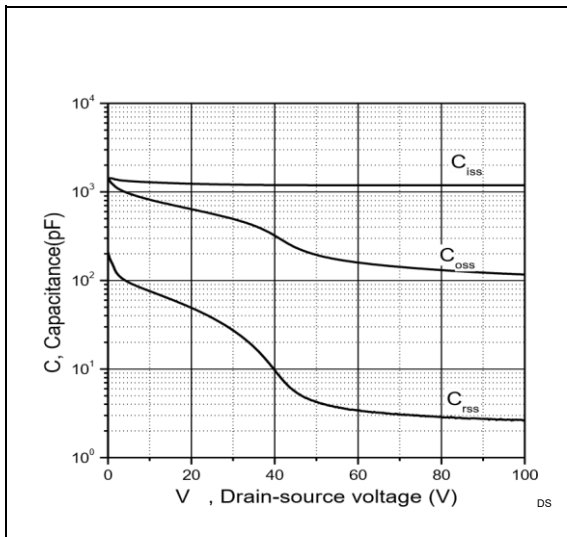


Figure 3, Typ. capacitances

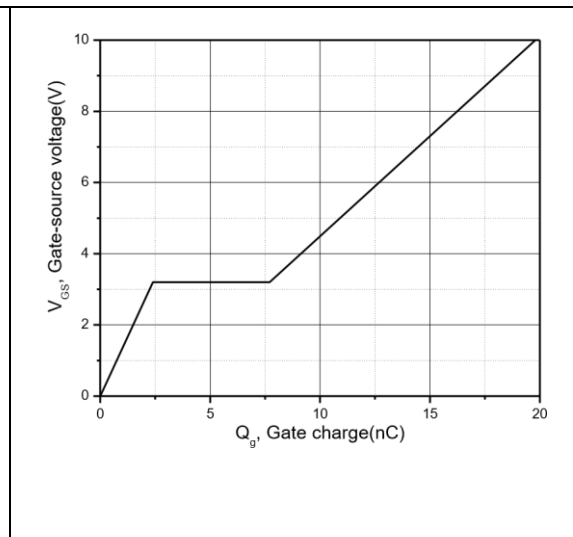


Figure 4, Typ. gate charge

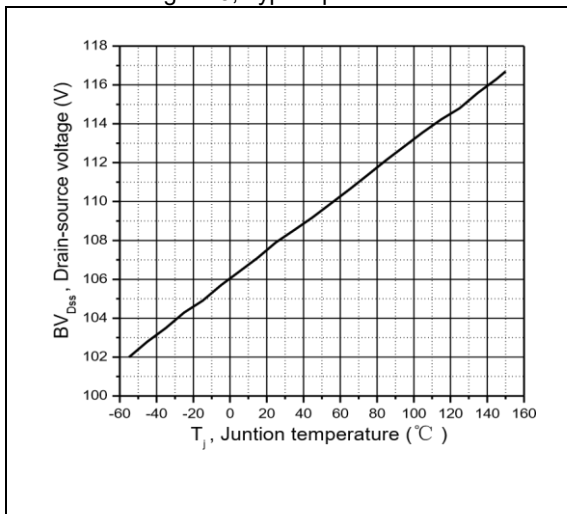


Figure 5, Drain-source breakdown voltage

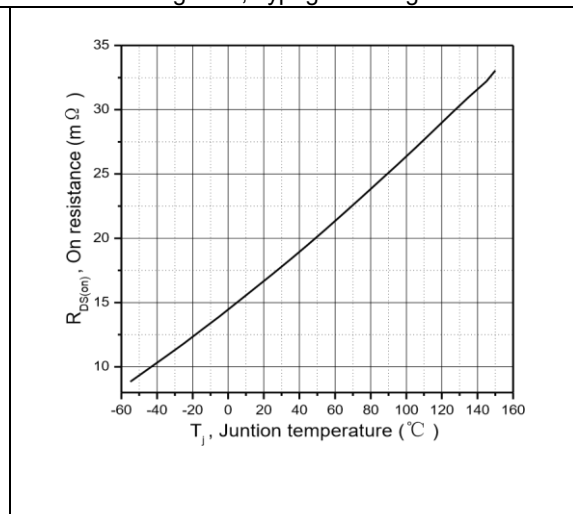


Figure 6, Drain-source on-state resistance

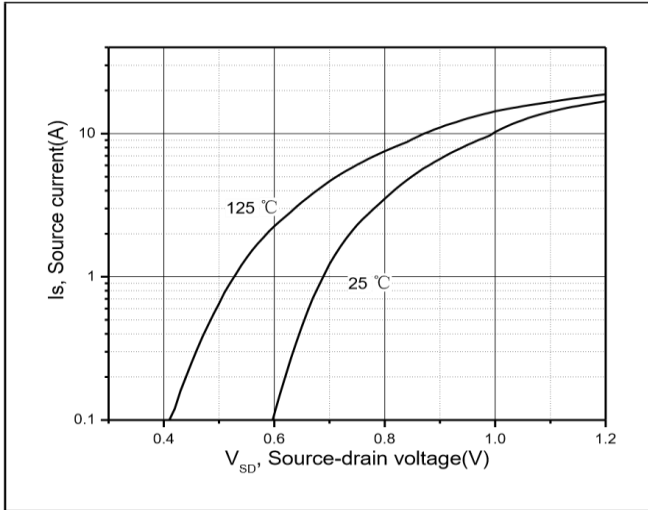


Figure 7, Forward characteristic of body diode

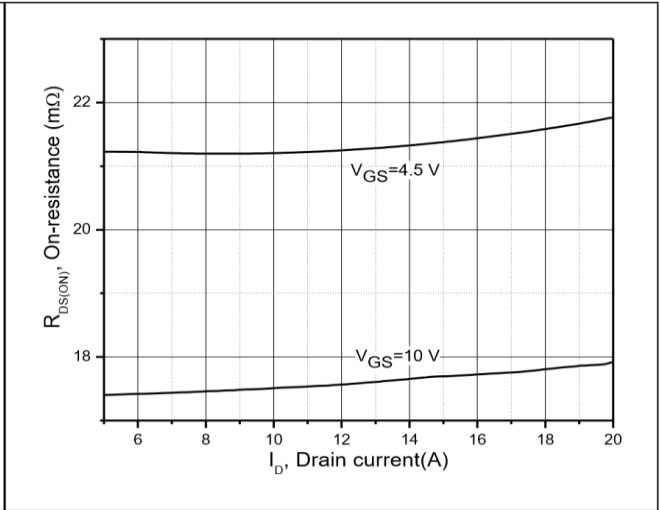


Figure 8, Drain-source on-state resistance

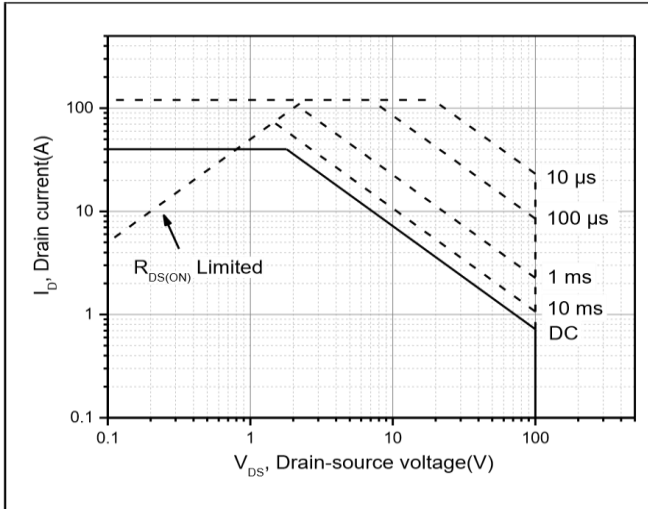


Figure 9, Safe operation area  $T_C=25\text{ }^\circ\text{C}$

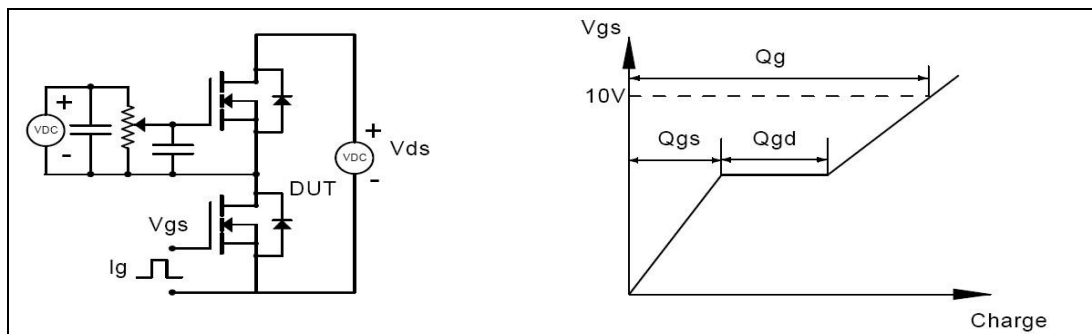


Figure 1, Gate charge test circuit & waveform

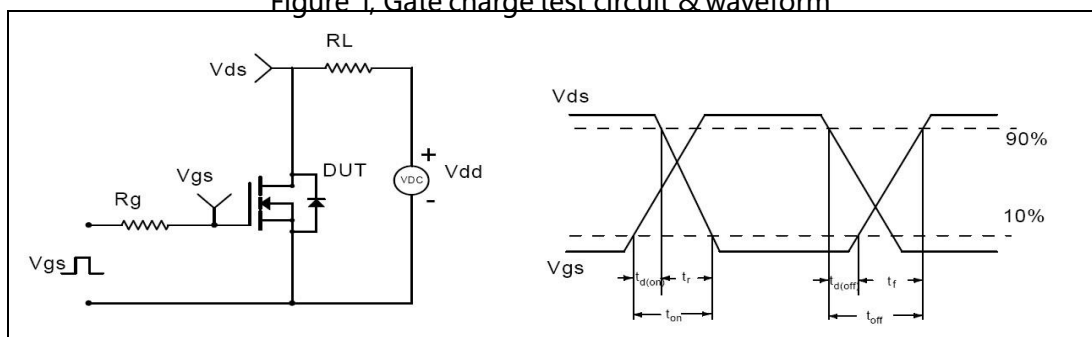


Figure 2, Switching time test circuit & waveforms

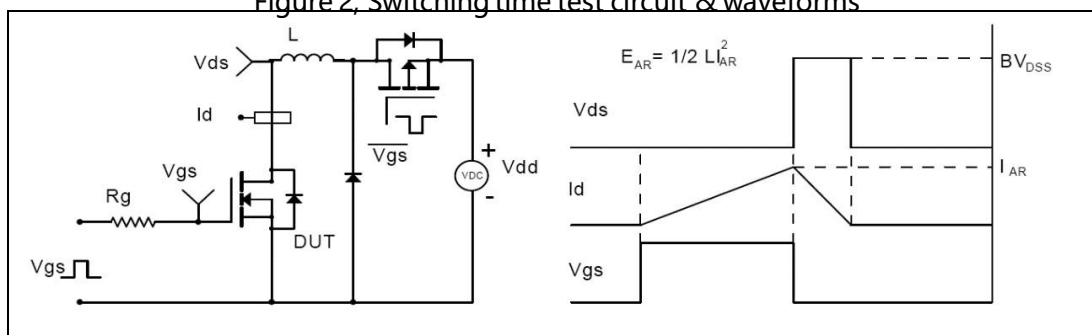


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

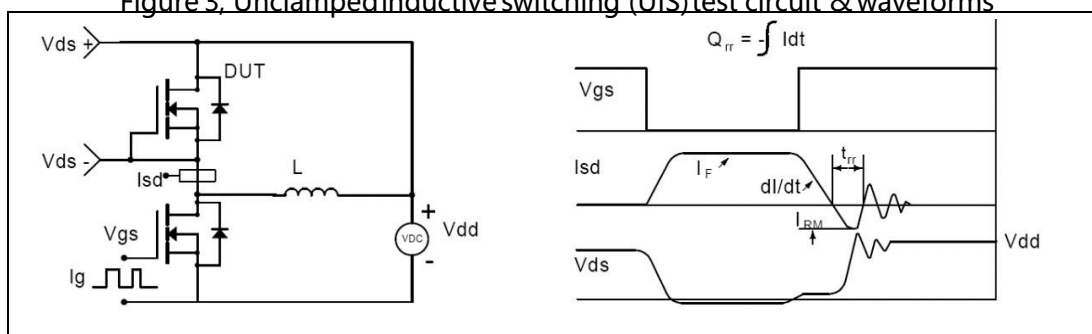
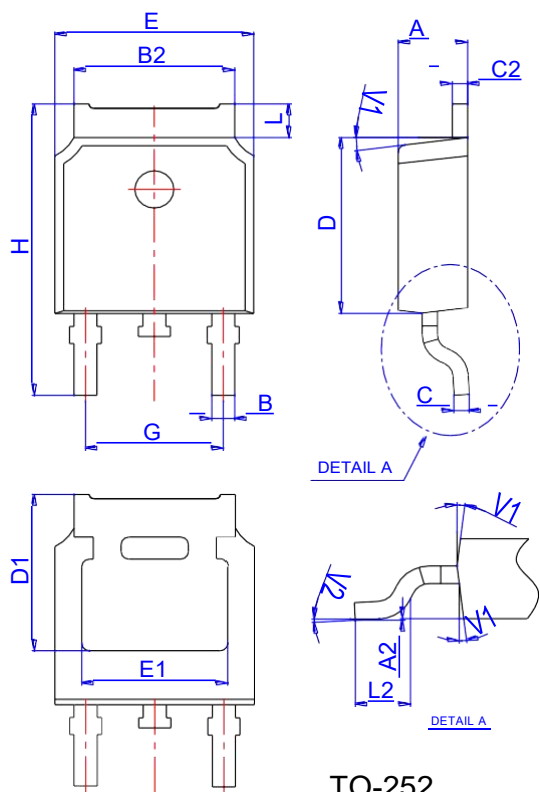


Figure 4, Diode reverse recovery test circuit & waveforms

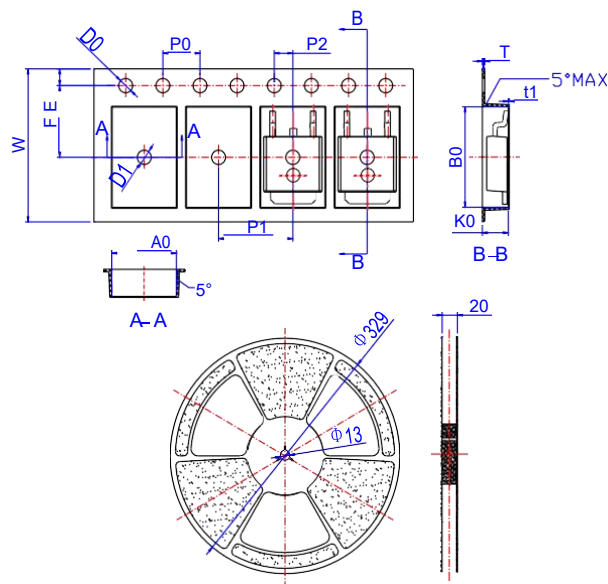
**Package Mechanical Data**



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**Reel Specification-TO-252**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583